

HZ-L Series

Silicon Epitaxial Planar Zener Diode for Low Noise Application

REJ03G0182-0200Z
(Previous: ADE-208-118A)
Rev.2.00
Mar.11.2004

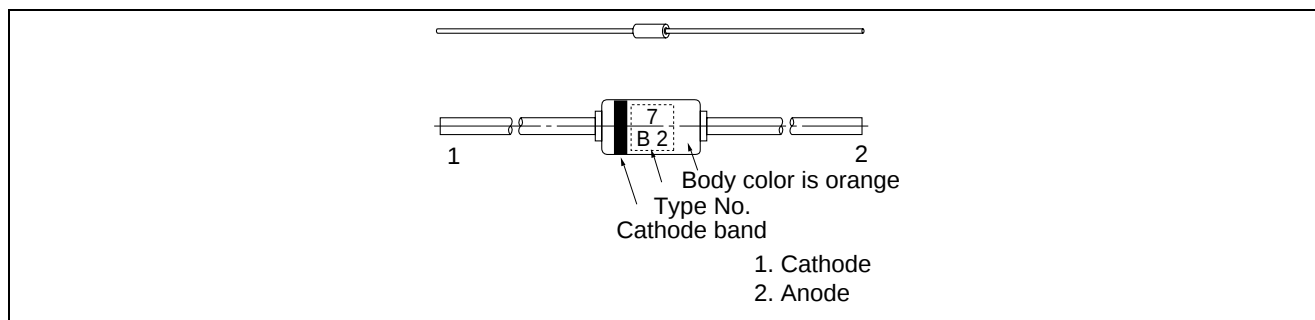
Features

- Diode noise level of this series is approximately 1/3-1/10 lower than the HZ series.
- Low leakage, low zener impedance and maximum power dissipation of 400 mW are ideally suited for stabilized power supply, etc.
- Wide spectrum from 5.2V through 38 V of zener voltage provide flexible application.

Ordering Information

Type No.	Mark	Package Code
HZ-L Series	Type No.	DO-35

Pin Arrangement



Absolute Maximum Ratings

(Ta = 25°C)

Item	Symbol	Value	Unit
Power dissipation	Pd	400	mW
Junction temperature	Tj	175	°C
Storage temperature	Tstg	-55 to +175	°C

Electrical Characteristics

(Ta = 25°C)

Type	Grade	Zener Voltage		Reverse Current		Dynamic Resistance	
		V _Z (V)* ¹		Test Condition	I _R (μA)	Test Condition	r _d (Ω)
		Min	Max	I _Z (mA)	Max	V _R (V)	Max
HZ6L	A1	5.2	5.5	0.5	1	2.0	150
	A2	5.3	5.6				
	A3	5.4	5.7				
	B1	5.5	5.8				80
	B2	5.6	5.9				
	B3	5.7	6.0				
	C1	5.8	6.1				60
	C2	6.0	6.3				
	C3	6.1	6.4				
HZ7L	A1	6.3	6.6	0.5	1	3.5	60
	A2	6.4	6.7				
	A3	6.6	6.9				
	B1	6.7	7.0				
	B2	6.9	7.2				
	B3	7.0	7.3				
	C1	7.2	7.6				
	C2	7.3	7.7				
	C3	7.5	7.9				
HZ9L	A1	7.7	8.1	0.5	1	6.0	60
	A2	7.9	8.3				
	A3	8.1	8.5				
	B1	8.3	8.7				
	B2	8.5	8.9				
	B3	8.7	9.1				
	C1	8.9	9.3				
	C2	9.1	9.5				
	C3	9.3	9.7				
HZ11L	A1	9.5	9.9	0.5	1	8.0	80
	A2	9.7	10.1				
	A3	9.9	10.3				
	B1	10.2	10.6				
	B2	10.4	10.8				
	B3	10.7	11.1				

Note: 1. Tested with DC.

Type	Grade	Zener Voltage		Reverse Current		Dynamic Resistance		
		V _Z (V)* ¹		Test Condition	I _R (μA)	Test Condition	r _d (Ω)	Test Condition
		Min	Max	I _Z (mA)	Max	V _R (V)	Max	I _Z (mA)
HZ11L	C1	10.9	11.3	0.5	1	8.0	80	0.5
	C2	11.1	11.6					
	C3	11.4	11.9					
HZ12L	A1	11.6	12.1	0.5	1	10.5	80	0.5
	A2	11.9	12.4					
	A3	12.2	12.7					
	B1	12.4	12.9					
	B2	12.6	13.1					
	B3	12.9	13.4					
	C1	13.2	13.7					
	C2	13.5	14.0					
	C3	13.8	14.3					
HZ15L	1	14.1	14.7	0.5	1	13.0	80	0.5
	2	14.5	15.1					
	3	14.9	15.5					
HZ16L	1	15.3	15.9	0.5	1	14.0	80	0.5
	2	15.7	16.5					
	3	16.3	17.1					
HZ18L	1	16.9	17.7	0.5	1	15.0	80	0.5
	2	17.5	18.3					
	3	18.1	19.0					
HZ20L	1	18.8	19.7	0.5	1	18.0	100	0.5
	2	19.5	20.4					
	3	20.2	21.1					
HZ22L	1	20.9	21.9	0.5	1	20.0	100	0.5
	2	21.6	22.6					
	3	22.3	23.3					
HZ24L	1	22.9	24.0	0.5	1	22.0	120	0.5
	2	23.6	24.7					
	3	24.3	25.5					
HZ27L	1	25.2	26.6	0.5	1	24.0	150	0.5
	2	26.2	27.6					
	3	27.2	28.6					
HZ30L	1	28.2	29.6	0.5	1	27.0	200	0.5
	2	29.2	30.6					
	3	30.2	31.6					
HZ33L	1	31.2	32.6	0.5	1	30.0	250	0.5
	2	32.2	33.6					
	3	33.2	34.6					
HZ36L	1	34.2	35.7	0.5	1	33.0	300	0.5
	2	35.3	36.8					
	3	36.4	38.0					

Note: 1. Tested with DC.

2. Type No. is as follows; HZ6A1L, HZ6A2L, HZ36-3L

Main Characteristic

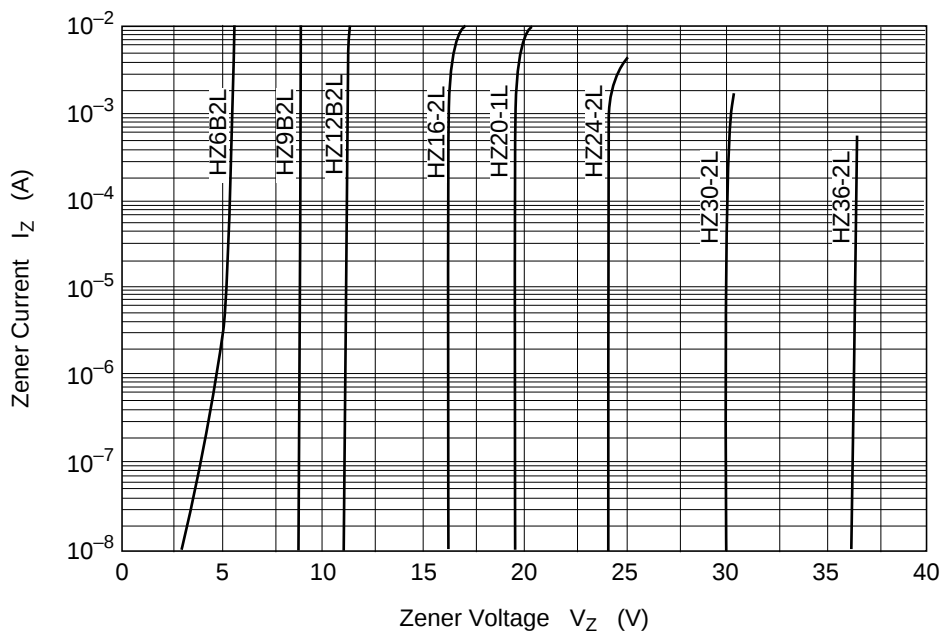


Fig.1 Zener current vs. Zener voltage

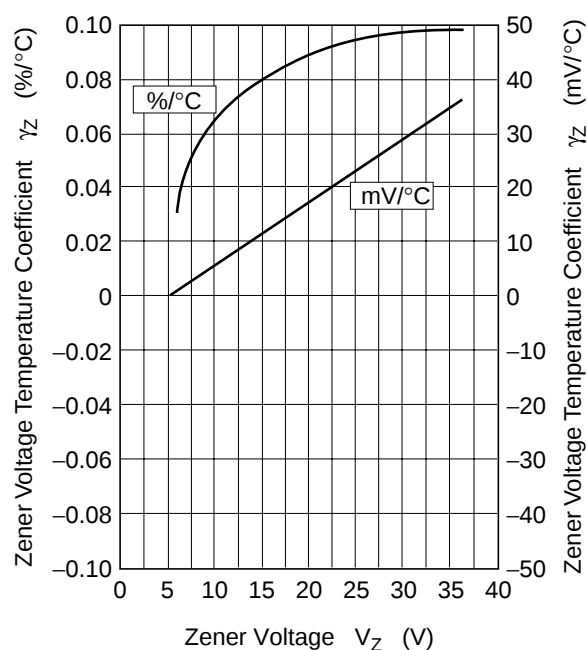


Fig.2 Temperature Coefficient vs. Zener voltage

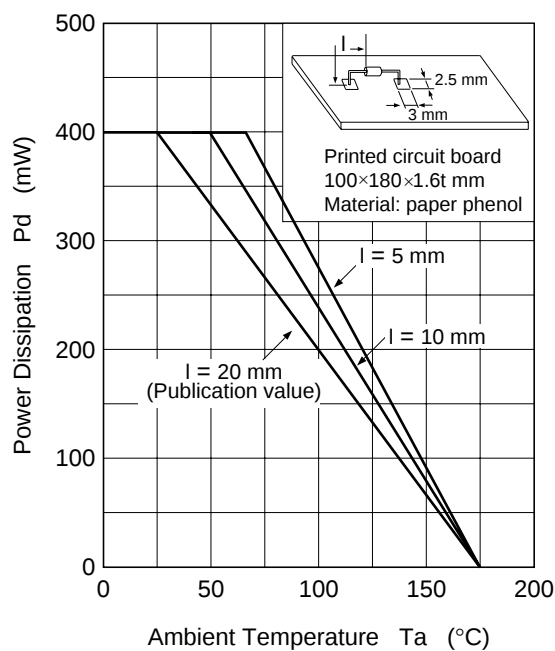
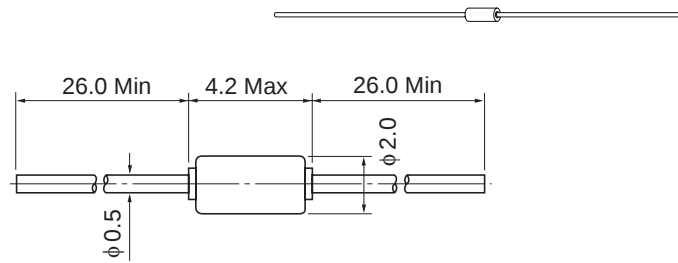


Fig.3 Power Dissipation vs. Ambient Temperature

Package Dimensions

As of January, 2003
Unit: mm



Package Code	DO-35
JEDEC	Conforms
JEITA	Conforms
Mass (reference value)	0.13 g

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